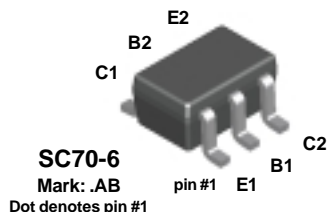
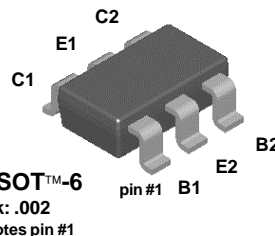


FFB3946



FMB3946

TRANSISTOR TYPE			
C1	B1	E1	NPN
C2	B2	E2	PNP



NPN & PNP General Purpose Amplifier

This complementary device is designed for use as a general purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and 100 MHz as an amplifier. Sourced from Process 23 and 66. See FFB3904 (NPN) and FFB3906 (PNP) for characteristics.

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CE0}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	200	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Characteristic	Max		Units
		FFB3946	FMB3946	
P_D	Total Device Dissipation	300	700	mW
	Derate above 25°C	2.4	5.6	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180	$^\circ\text{C}/\text{W}$

NPN & PNP General Purpose Amplifier

(continued)

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10\text{ mA}, I_B = 0$	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\ \mu\text{A}, I_E = 0$	40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\ \mu\text{A}, I_C = 0$	5.0			V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 30\text{ V}, I_E = 0$			50	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0\text{ V}, I_C = 0$			50	nA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 100\ \mu\text{A}, V_{CE} = 1.0\text{ V}$ $I_C = 1.0\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 50\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V}$	40		300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$			0.25	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$			0.9	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 10\text{ mA}, V_{CE} = 20\text{ V},$ $f = 100\text{ MHz}$		200		MHz
C_{obo}	Output Capacitance	$V_{CB} = 5.0\text{ V}, f = 100\text{ kHz}$		4.5		pF
C_{ibo}	Input Capacitance	$V_{CB} = 5.0\text{ V}, f = 100\text{ kHz}$		10		pF

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

FFB3946 / FMB3946

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DOME TM	ISOPLANAR TM	Quiet Series TM	
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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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